



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	Ι _D Τ _A = 25°C
20V	3.0 Ω @ V _{GS} = 4.5V	240mA
	6.0 Ω @ V _{GS} = 1.8V	180mA

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions

Features

- Dual N-Channel MOSFET
- Low On-Resistance:
 - 3.0 Ω @ 4.5V
 - 4.0 Ω @ 2.5V
 - 6.0 Ω @ 1.8V
 - 10 Ω @ 1.5V
- Very Low Gate Threshold Voltage, 1.05V max
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- ESD Protected Gate (HBM 300V)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

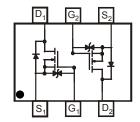
- Case: SOT963
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.0027 grams (approximate)





SOT963

Top View



Top View Schematic and Transistor Diagram

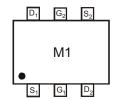
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN26D0UDJ-7	SOT963	10.000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information (Note 5)



M1 = Product Type Marking Code

Notes: 5. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±10	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	240 190	mA
Continuous Drain Current (Note 6) V _{GS} = 1.8V	Steady State	T _A = +25°C T _A = +70°C	I _D	180 140	mA
Pulsed Drain Current - T _P = 10μs			I _{DM}	805	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_D	300	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ hetaJA}$	409	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 100 \mu A$	
Zero Gate Voltage Drain Current @ T _C = +25°C	I _{DSS}	_		500	nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Body Leakage	1	_	_	±1	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$	
Gale-Body Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.45	8.0	1.05	V	$V_{DS} = V_{GS}$, $I_{D} = 250 \mu A$	
		_	1.8	3.0		$V_{GS} = 4.5V, I_D = 100mA$	
	R _{DS} (ON)		2.5	4.0	Ω	$V_{GS} = 2.5V, I_D = 50mA$	
Static Drain-Source On-Resistance			3.4	6.0		$V_{GS} = 1.8V, I_D = 20mA$	
			4.7	10.0		$V_{GS} = 1.5V, I_D = 10mA$	
		_	9.5	_		V _{GS} = 1.2V, I _D = 1mA	
Forward Transconductance	Y _{fs}	180	240	_	mS	$V_{DS} = 10V, I_{D} = 0.1A$	
Source-Drain Diode Forward Voltage		0.5	8.0	1.0	V	$V_{GS} = 0V, I_{S} = 10mA$	
Source-Drain Diode Forward Voltage V_{SD} 0.5 0.8 1.0 V_{SS} = 0V, I_{S} = 10mA DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		14.1		pF	1/ 45)/ 1/ 0)/	
Output Capacitance	Coss	_	2.9		pF	$V_{DS} = 15V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		1.6		pF		
SWITCHING CHARACTERISTICS, V _{GS} = 4.5V (Note 8)							
Turn-On Delay Time	t _{d(on)}	_	3.8				
Rise Time	t _r		7.9	_	ns	$V_{GS} = 4.5V, V_{DD} = 10V$	
Turn-Off Delay Time	t _{d(off)}	_	13.4	_	115	I_D = 200mA, R_G = 2.0 Ω	
Fall Time	t _f		15.2				

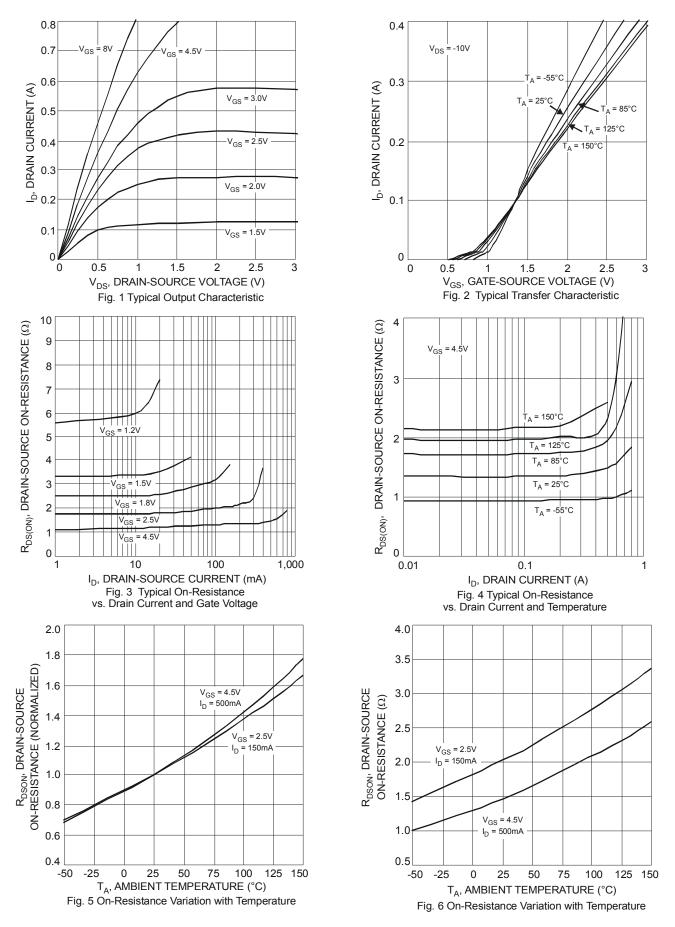
Notes:

^{6.} Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch with minimum recommended pad layout; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.

7. Short duration pulse test used to minimize self-heating effect.

8. Switching characteristics are independent of operating junction temperature. Guaranteed by design, not subject to production testing.







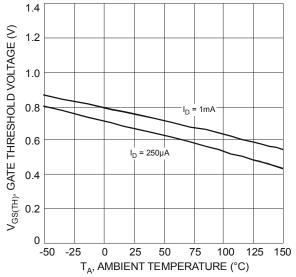
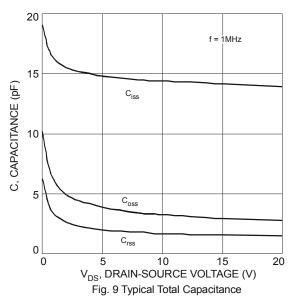
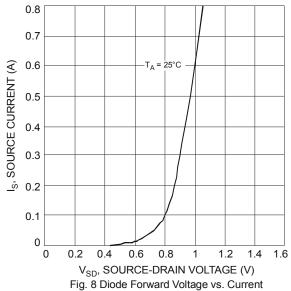


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





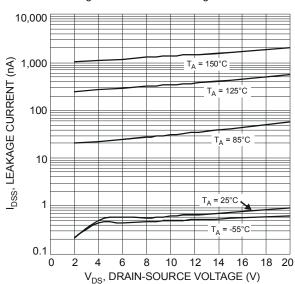
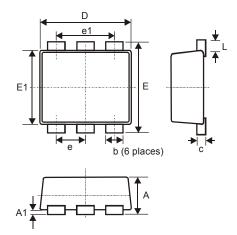


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

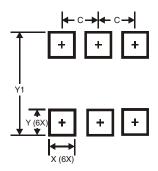


SOT963					
Dim	Min	Max	Тур		
Α	0.40	0.50	0.45		
A1	0	0.05	-		
С	0.120	0.180	0.150		
D	0.95	1.05	1.00		
E	0.95	1.05	1.00		
E1	0.75	0.85	0.80		
L	0.05	0.15	0.10		
b	0.10	0.20	0.15		
е	0.35 Typ				
e1	0.70 Typ				
All Dimensions in mm					



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.350
Х	0.200
Y	0.200
Y1	1.100

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